Universidad Autónoma de Coahuila

Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15128916***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***PEDRO FRAIRE SOLÍS***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

Universidad Autónoma de Coahuila

Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15132525***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JULIO CÉSAR LOZANO ALMAGUER***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15158174***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JORGE LUIS DÍAZ ENRÍQUEZ***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15149897***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JULIO CÉSAR GARCÍA CASTILLO***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15133897***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***VÍCTOR MANUEL GARCÍA CARRILLO***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15132740***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JOVANA SOLEDAD GARCÍA REYES***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15141730***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***VÍCTOR MANUEL PUENTES RODRÍGUEZ***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15153534***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JOSÉ ANTONIO RINCÓN ACOSTA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15149344***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***FABIÁN ALONSO SOTO LUNA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15140545***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***MAYRA SELENE MIRELES CARDOZA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15315202***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***ALAN M. CABRERA MORA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***13056433***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***DANIEL ALEJANDRO CARRILLO HERNÁNDEZ***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15122162***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***ORLANDO BARBOZA GARCÍA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***10069634***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***EDUARDO TORRES GOITIA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15157355***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***VICTOR SIFUENTES VARGAS***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***14576492***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***JONATHAN RODRÍGUEZ CHÁVEZ***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***15129708***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***LUIS FERNANDO CASTAÑEDA QUIROGA***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

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Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***14317737***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***VANESA IRANÍ MORA MORENO***		

Instructions

1. The student should submit the homework on or before the due date. (LATE SUBMISSION = 0 MARKS)
2. Answers should be hand written on a A4 or a letter size bond papers. (20% of the marks obtained will be reduced)
3. The student should print his/her corresponding question-paper and staple it along with his/her answer sheets. (20% of the marks obtained will be reduced)
4. In the calculations, the student should maintain at least a precision of 3 decimal places with a correct rounding. (20% of the marks obtained will be reduced)

Questions

Design and perform an experiment to observe the V-I characteristics of p-n junction diode. Carryout in the following two stages.

Stage 1 Design the experiment and prepare the report with the following points. (10 points)

1. Objective (2 points)
2. Experimental setup, i.e. circuit diagram (2 points)
3. Apparatus required (2 points)
   (a) Materials
   (b) Equipment
4. Procedure (4 points)

Stage 2 Perform the experiment and finish the report by including the following points. (10 points)

1. Collected data (2 points)
2. Plot the obtained data on a graph-sheet (4 points)
3. Results and discussions (2 points)
4. Conclusions (2 points)

Universidad Autónoma de Coahuila

Facultad de Ingeniería Mecánica y Eléctrica

Unidad Torreón

Subject	Semiconductor physics	Group	4A
Degree	Electrical engineering	Date	03 & 17 /02/2017
Exam / Homework	Homework 2 & 3: V-I characteristics of p-n junction diode	Registration #	***7272835***
Professor's name	Suresh Kumar Gadi	Marks Obtained	_____ /10
Student's name	***CASTREJÓN ALFARO SERGIO PABLO***		

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